

### 150V N-Channel Enhancement Mode MOSFET

Voltage 150 V Current 18 A

#### **Features**

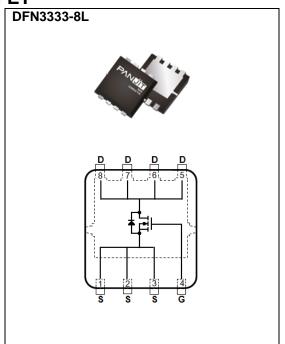
- RDS(ON), VGS@10V, ID@10A< $50m\Omega$
- RDS(ON), VGS@7V, ID@6A< $55m\Omega$
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	150	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current(Note 3)	T <sub>C</sub> =25°C		18		
	T <sub>C</sub> =100°C	I <sub>D</sub>	13	Α	
Pulsed Drain Current(Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	50		
Power Dissipation	T <sub>C</sub> =25°C	D.	50	W	
	T <sub>C</sub> =100°C	Po	25		
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C		4.5	А	
	T <sub>A</sub> =70°C	l <sub>D</sub>	3.7		
Power Dissipation	T <sub>A</sub> =25°C	PD	2.5	W	
	T <sub>A</sub> =70°C		1.8		
Single Pulse Avalanche Current <sup>(Note 5)</sup>		I <sub>AS</sub>	18	А	
Single Pulse Avalanche Energy <sup>(Note 5)</sup>		E <sub>AS</sub>	55	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C	
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	R <sub>θ</sub> JC	3.7	°C/W	
	Junction to Ambient	R <sub>θJA</sub>	60		



### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	S V <sub>GS</sub> =0V, I <sub>D</sub> =250uA 150		-	-		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	3	4	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	40	50	mΩ	
		V <sub>GS</sub> =7V, I <sub>D</sub> =6A	-	42	55		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
Dynamic <sup>(Note 6)</sup>				•			
Total Gate Charge	$Q_g$	.,	ı	22	29	nC	
Gate-Source Charge	Qgs	V <sub>DS</sub> =75V, I <sub>D</sub> =10A,	-	7	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	6	-		
Input Capacitance	Ciss		-	1116	1450	pF	
Output Capacitance	Coss	V <sub>DS</sub> =75V, V <sub>GS</sub> =0V,	-	81	142		
Reverse Transfer Capacitance	Crss	f=1MHz	-	23	-		
Gate resistance	Rg	f=1MHz	-	0.8	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>	.,,	-	8.4	-		
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =75V, I <sub>D</sub> =10A,	-	14	-	ns	
Turn-Off Delay Time	td(off)	$V_{GS}=10V, R_{G}=3\Omega$	-	17	-		
Turn-Off Fall Time	tf	(Note 2,3)	-	11	-		
Drain-Source Diode	•				•		
Diode Forward Current	Is	T 0500	-	-	18	A	
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> =25°C	-	-	50		
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =20A, V <sub>GS</sub> =0V	-	0.9	1.3	V	
Reverse Recovery Time	Trr	V <sub>DD</sub> =75V,V <sub>GS</sub> =0V	-	58	-	ns	
Reverse Recovery Charge	Qrr	I <sub>S</sub> =20A,dI <sub>S</sub> /dt=100A/us	-	90	-	nC	

#### NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an  $R_{\theta JC}$ = 3.7°C/W.
- 4. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5.  $E_{AS}$  is calculated based on the condition of L=1mH,  $I_{AS}$ =10.5A,  $V_{DD}$ =30V,  $V_{GS}$ =10V. 100% test at L=0.1mH,  $I_{AS}$ =18A in production.
- 6. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**

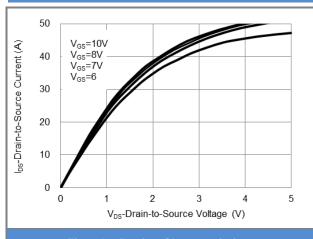


Fig.1 On-Region Characteristics

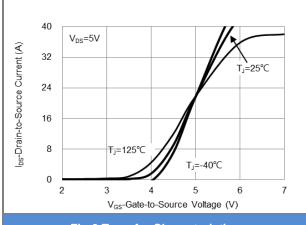


Fig.2 Transfer Characteristics

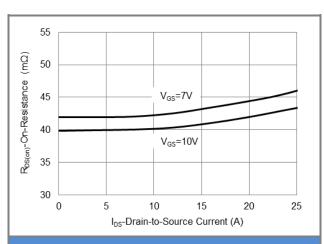


Fig.3 On-Resistance vs. Drain Current

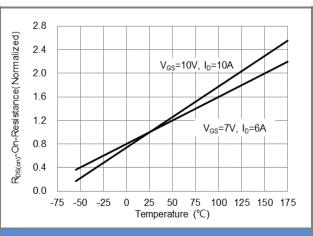
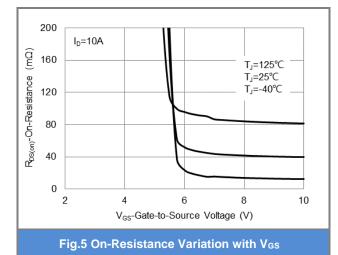
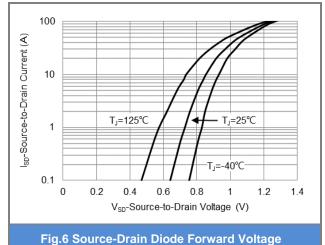


Fig.4 On-Resistance vs. Junction temperature







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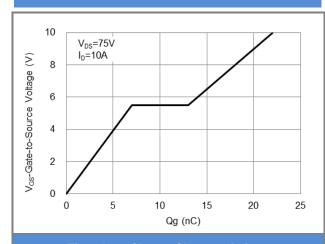


Fig.7 Gate-Charge Characteristics

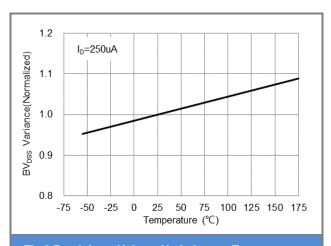


Fig.8 Breakdown Voltage Variation vs. Temperature

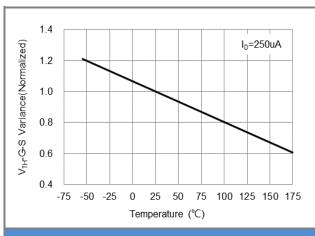


Fig.9 Threshold Voltage Variation with Temperature

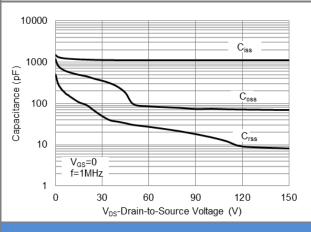
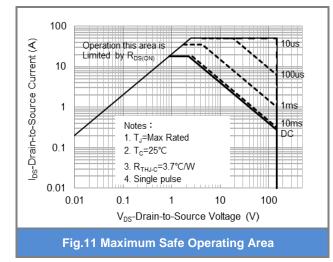


Fig.10 Capacitance vs. Drain-Source Voltage



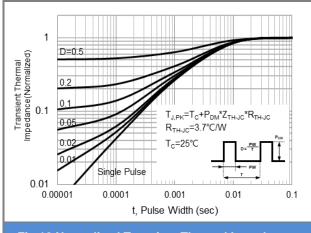


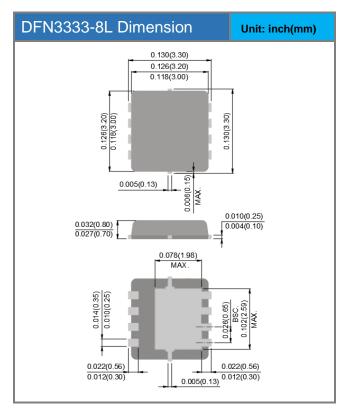
Fig.12 Normalized Transient Thermal Impedance

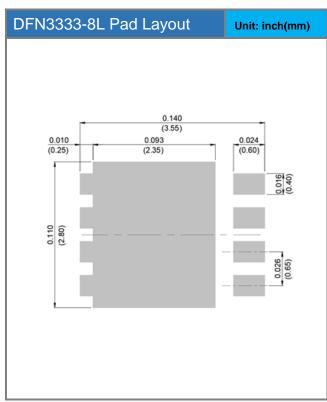


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ4594P-AU	DFN3333-8L	5K pcs / 13" reel	4594	

### **Packaging Information & Mounting Pad Layout**







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